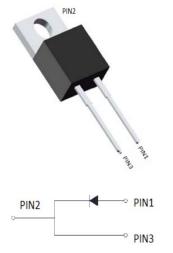


YJD106506PQG2Q

Silicon Carbide Schottky Diode

V _{RRM}	650 V
I _F (135°C)	10 A
Q _C	25 nC



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- AEC-Q101 qualified
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

- Package: TO-220AC Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant, halogen-free
- Terminals: Tin plated leads
- Polarity: As marked

■Maximum Ratings (T_c=25[°]C Unless otherwise specified)

PARAMTETER	SYMBOL	UNIT	VALUE
Device marking code			D106506PQG2
Reverse voltage (repetitive peak) @ T _j =25°C	V _{RRM}	V	650
Reverse voltage (Surge Peak) @ Tj=25°C	V _{RSM}	V	650
Reverse voltage (DC) @ Tj=25°C	V _{DC}	V	650
Continuous forward current @ T _c =25°C			21
Continuous forward current @ T_c =135°C	I _F	А	10
Continuous forward current @ T _c =157°C			6
Non-repetitive peak forward surge current @ T _c =25°C, tp=10ms, Half Sine Wave	I _{FSM}	А	65
Power Dissipation@ T _c =25°C		14/	84
Power Dissipation@ T _c =110°C	P _{TOT}	W	36
i²t Value@ Tc=25°C ,tp=10ms	∫ i²dt	A ² S	21
Operating junction and Storage temperature range	T _j ,T _{stg}	°C	-55 to +175

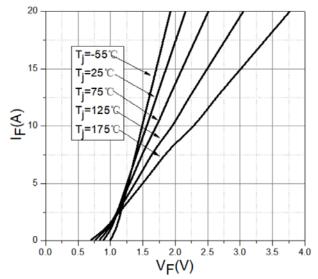
Electrical Characteristics

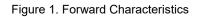
PARAMTETER	SYMBOL	UNIT	TEST CONDITIONS	Тур.	Max.		
Forward voltage drap	M	V _F V	I _F =6A, T _j =25°C	1.31	1.5		
Forward voltage drop	VF		I _F =6A, T _j =175°C	1.65	-		
Reverse leakage current	kage current I _R μ				V _R =650V, T _j =25°C	0.5	25
Neverse leakage current		μA	V _R =650V, T _j =175°C	5	-		
Total capacitive charge	Qc	nC	V_R =400V, T _j =25°C , QC= \int_0^{VR} C(V)dV	25	-		
	icitance C		V _R =0V, f=1MHZ	378	-		
Total capacitance		pF	V _R =200V, f=1MHZ	51	-		
			V _R =400V, f=1MHZ	49	-		
Capacitance Stored Energy	Ec	μJ	V _R =400V	3	-		

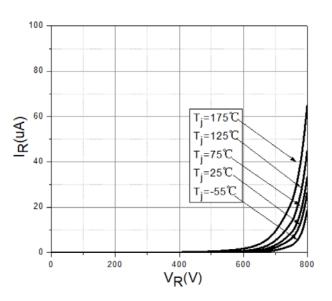
■Thermal Characteristics (Ta=25°C Unless otherwise specified)

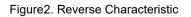
PARAMETER	SYMBOL	UNIT	Value
Thermal resistance	R _{øJ-C}	°C W	1.78

■Typical Characteristics









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YJD106506PQG2Q

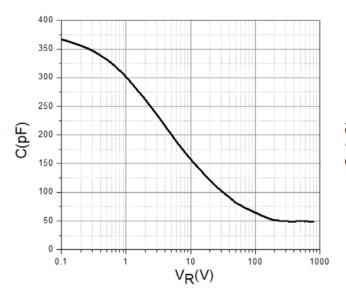
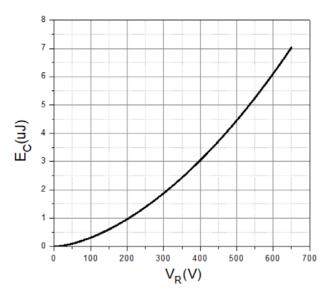
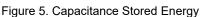


Figure 3. Capacitance vs. Reverse Voltage





80 70 10% Duty 20% Duty 60 30% Duty 50% Duty 50 I_{F(peak)}(A) 70% Duty DC 40 30 20 10 0 L 25 50 75 100 125 150 175 T_c(℃) Figure 7. Current Derating

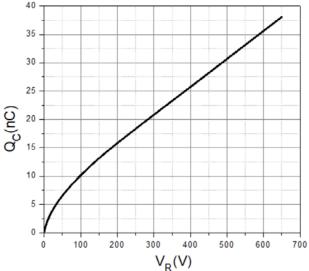
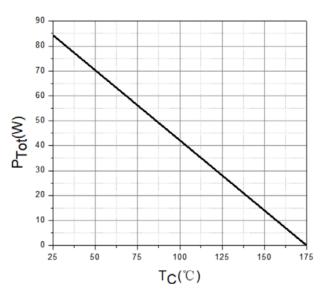
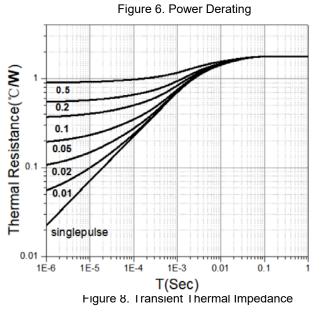


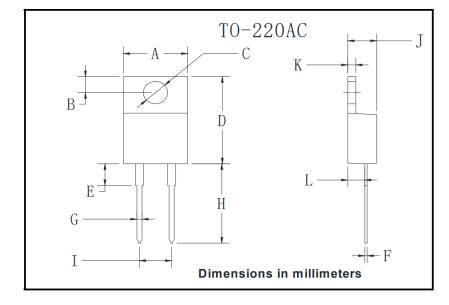
Figure 4. Total Capacitance Charge vs. Reverse Voltage







Outline Dimensions



TO-220AC				
Dim	Min	Max		
А	9.95	10.35		
В	2.55	2.95		
С	3.75	4.05		
D	14.95	15.25		
E	3.75	4.25		
F	0.26	0.5		
G	0.68	0.94		
Н	13.3	13.9		
I.	4.86	5.26		
J	4.38	4.78		
К	1.14	1.4		
L	2.37	2.79		

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